

20V N-Channel MOSFET w/ESD Protected



SOP-8

Pin Definition:

- 1. Source
- 2. Source
- 3. Source
- 4. Gate
- 5, 6, 7, 8. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
20	25 @ V _{GS} = 4.5V	4.5
	30 @ V _{GS} = 2.5V	3.5
	65 @ V _{GS} = 1.8V	2.0

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance
- ESD Protect 2KV

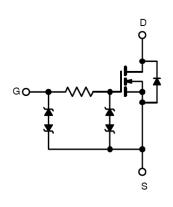
Application

- Specially Designed for Li-on Battery Packs
- Battery Switch Application

Ordering Information

Part No.	Package	Packing
TSM7401CS RL	SOP-8	2.5Kpcs / 13" Reel

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	20	V	
Gate-Source Voltage		V_{GS}	±12	V	
Continuous Drain Current		I _D	8	Α	
Pulsed Drain Current		I _{DM}	30	Α	
Continuous Source Current (Diode Co	nduction) ^{a,b}	I _S	1.4	Α	
Maximum Power Dissipation	Ta = 25°C	- P _D	2.5	W	
	Ta = 75°C		1.3		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	R⊖ _{JF}	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RO _{JA}	50	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, $t \le 5$ sec.



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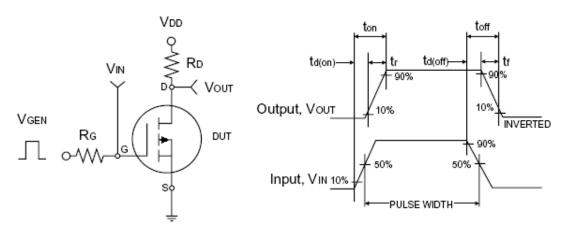


Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	V _{GS(TH)}	0.6	0.8	1.0	V
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I _{GSS}			±10	uA
Zero Gate Voltage Drain Current	$V_{DS} = 16V, V_{GS} = 0V$	I _{DSS}			1.0	uA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I _{D(ON)}	30			Α
	V _{GS} = 4.5V, I _D = 4.5A	17	25			
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 3.5A$	R _{DS(ON)}		21	30	mΩ
	$V_{GS} = 1.8V, I_D = 2.0A$			34	65	
Forward Transconductance	$V_{DS} = 10V, I_D = 4.5A$	g _{fs}		30		S
Diode Forward Voltage	I _S = 2A, V _{GS} = 0V	V_{SD}		0.6	1.2	V
Dynamic ^b						
Total Gate Charge	\/ - 40\/ - 4.54	Q_g	1	15	20	
Gate-Source Charge	$V_{DS} = 10V, I_D = 4.5A,$ $V_{GS} = 4.5V$	Q_gs	1	3.4		nC
Gate-Drain Charge	V _{GS} - 4.5 V	Q_{gd}		1.2		
Input Capacitance	\\ -40\\\\\ -0\\	C _{iss}		950		
Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	Coss		450		pF
Reverse Transfer Capacitance	7 I = 1.UIVIDZ	C _{rss}		135		
Switching ^c						
Turn-On Delay Time	10V D 100	t _{d(on)}		140	200	
Turn-On Rise Time	$V_{DD} = 10V, R_L = 10\Omega,$	t _r		210	250	20
Turn-Off Delay Time	$I_D = 1A, V_{GEN} = 4.5V,$	t _{d(off)}		3700	4800	nS
Turn-Off Fall Time	$R_G = 6\Omega$	t _f		2000	2600	

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms



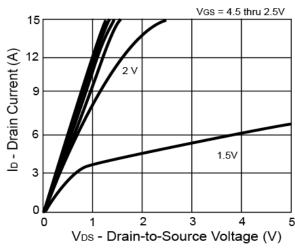




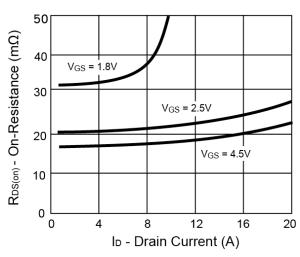
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Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

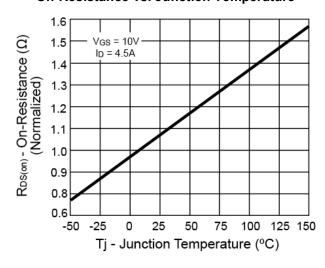




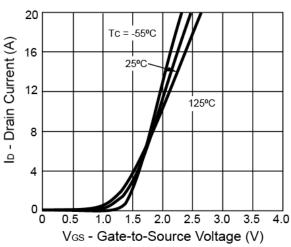
On-Resistance vs. Drain Current



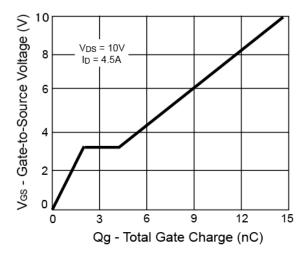
On-Resistance vs. Junction Temperature



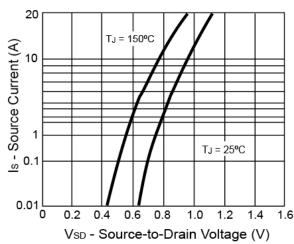
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



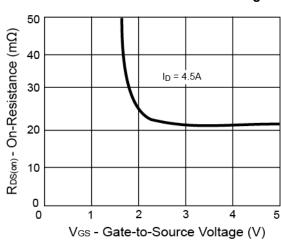


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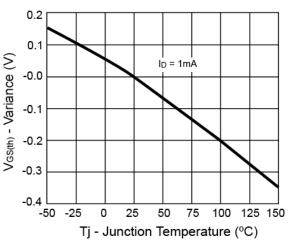


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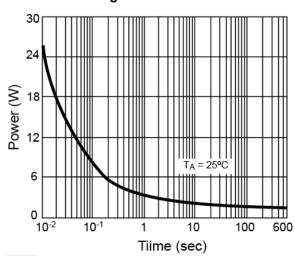
On-Resistance vs. Gate-Source Voltage



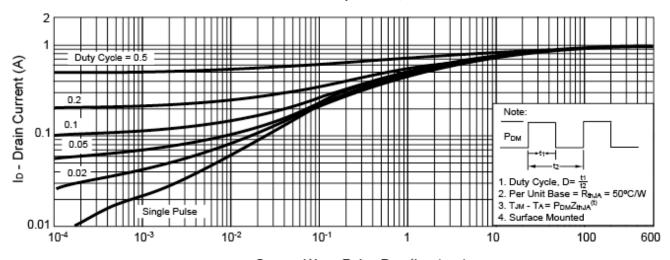
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



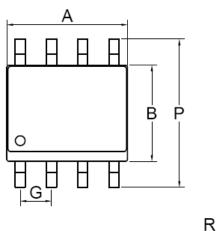
Square Wave Pulse Duration (sec)

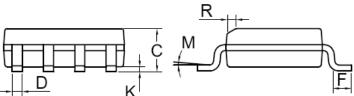


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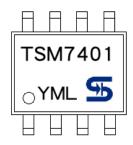
SOP-8 Mechanical Drawing





SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.05	BSC	
K	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

Marking Diagram



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code



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